

ABSTRACT OF THE DISCLOSURE

5 The first present invention provides a nitride based semiconductor photo-luminescent device having an active layer having a quantum well structure, the active layer having both at least a high dislocation density region and at least a low dislocation density region lower in dislocation density than the high dislocation density region, wherein the low dislocation density region includes a current injection
10 region into which a current is injected, and the active layer is less than $1 \times 10^{18} \text{ m}^{-3}$ in impurity concentration.